IN THE CLAIMS:

1. (Currently amended) A slurry for chemical mechanical polishing (CMP) ~~of a copper or silver containing film~~, comprising:

a solution including a halogen comprising salt and at least one species selected from the group of diatomic VIIA elements consisting of a ~~polyhalide ion,~~ I_2, Br_2 and F_2 ~~for reacting with said copper or silver film to form a soft layer on a surface of said film, said soft layer having a hardness less than said copper or silver film~~.

2. (Currently amended) The slurry of claim 1, wherein said diatomic VIIA element ~~soft layer~~ comprises I_2 ~~a copper or silver halide~~.

3. (Currently amended) The slurry of claim 2, wherein a pH of said solution is <9 ~~said copper or silver halide comprises copper iodide (CuI) or silver iodide (AgI)~~.

4. (Original) The slurry of claim 1, wherein said slurry includes a plurality of soft particles.

5. (Original) The slurry of claim 4, wherein said plurality of soft particles comprise polymer or nano-porous particles.

6. (Original) The slurry of claim 5, wherein said plurality of soft particles comprise at least one selected from the group consisting of polystyrene, polytetrafluoroethylene, polyamide, silver and porous silica.

7. (Currently amended) The slurry of claim 1, wherein said solution further comprises at least one selected from the group consisting of ~~iodine, bromine, fluorine,~~ HI, [KIO_3,] sulfuric acid, hydrochloric acid and carbonic acid.

8. (Previously presented) The slurry of claim 1, wherein a pH of said slurry is from 2 to 9.

9. (Currently amended) The slurry of claim 1, further comprising at least one etchant ~~for removing a copper or silver oxide or a carbon containing film disposed on or in contact with said copper or silver film~~.

10. (Original) The slurry of claim 9, wherein said etchant comprises an acid.

11. (Original) The slurry of claim 10, wherein said acid comprises at least one selected from the group consisting of nitric acid, acetic acid, sulfuric acid, hydroxy acid, hydrochloric acid, hydrofluoric acid, carboxylic acid, citric acid, malic acid, malonic acid, succinic acid, phtalic acid, tartaric acid, dihydroxysuccinic acid, lactic acid, malic acid, fumaric acid, adipic acid, glutaric acid, oxalic acid, benzoic acid, propionic acid, butyric acid, EDTA and valeric acid.

12. (Cancelled)

13. (Currently amended) The slurry of claim 1, further comprising at least one nitrogen containing organic passivating additive.

14. (Currently amended) The slurry of claim 13, wherein said passivating additive is at least one selected from the group consisting of [BTA and TTA] azoles, amines, thiols and mercaptans.

15. (Currently amended) The slurry of claim [1] 14, [further comprising at least one salt] wherein said azole is BTA or TTA.

16. (Cancelled)

17. (Original) The slurry of claim 1, further comprising at least one chelating agent.

18. (Original) The slurry of claim 17, wherein said chelating agent is at least one selected from the group consisting of EDTA, en, acac, phen and oxalate ions.

19. (Currently amended) The slurry of claim 1, wherein [a selectivity of a CMP process using said slurry is at least 100 for removal of said copper or silver film relative to a layer comprising tantalum or titanium] said halide salt comprises at least one selected from the group consisting of iodides, chlorides and bromides .

20. (Cancelled)

21. (Cancelled)

22. (Cancelled)

23. (Cancelled)

24. (Original) The slurry of claim 1, further comprising at least one surfactant.

25. (Original) The slurry of claim 24, wherein said surfactant is at least one selected from the group consisting of non-ionic, anionic, cationic and zwitterionic surfactants.

26. (Previously presented) The slurry of claim 25, wherein said surfactant is at least one selected from the group consisting of SDS, SAS, CTAB, octylphenol ethylene oxide condensate and polyoxyethylene sorbitan monooleate, a water soluble copolymer of an average molecular weight of approximately 15,000 consisting of a-olefins and dicarboxylic acids, partially esterified with an ethoxilated alcohol, and CTAC.

27. (Original) The slurry of claim 1, further comprising at least one polymer additive.

28. (Original) The slurry of claim 27, wherein said polymer additive is at least one selected from the group consisting of polyethylene oxide (PEO), polyacrylic acid (PAA), polyacryamide (PAM), polyvinylalcohol (PVA) and polyalkylamine (PAH).

29. (Original) The slurry of claim 1, wherein said slurry is a non-aqueous slurry.

30. (Cancelled)

31. (Cancelled)

32. (Cancelled)

33. (Currently amended) A slurry for chemical mechanical polishing (CMP) ~~of a copper or silver containing film~~, comprising:

a solution including at least one nitrogen containing organic passivating additive ~~providing at least one species selected from the group consisting of a polyhalide ion,~~ and I_2 , said solution having a pH of <9 ~~, Br_2 and F_2 for reacting with said copper or silver film to form a soft layer on a surface of said film, said soft layer having a hardness less than said copper or silver film; and~~

~~abrasive particles in a concentration of less than 1% by weight~~.

34. (Currently amended) The slurry of claim 33, wherein said [at least one] passivating additive comprises at least one selected from the group consisting of azoles, amines, thiols and mercaptans ~~concentration of said abrasive particles is less than approximately 0.1% by weight~~.

35. (Currently amended) The slurry of claim ~~33~~ 34, wherein said [passivating additive is at least one selected from the group consisting of] azole is BTA [and] or TTA ~~abrasive particles comprise at least one selected from the group consisting of silica, alumina, zirconia, carbon and yttria~~.

36. (Currently amended) ~~A~~ The slurry of claim 33, further comprising at least one surfactant. ~~for chemical mechanical polishing (CMP) of a structure including a copper or silver film and a silicon dioxide, alumina or a dielectric film which has a dielectric constant less than silicon dioxide, wherein said slurry includes at least one species selected from the group consisting of a polyhalide ion, I_2, Br_2 and F_2 and provides a selectivity for a CMP process of at least 200 for removal of said copper or silver film relative to said dielectric film~~.

37. (Currently amended) The ~~A~~ slurry of claim 33, further comprising a halogen comprising salt ~~for chemical mechanical polishing (CMP) of a structure including a copper or silver film and a titanium or tantalum based barrier film, including at least one species selected from the group consisting of a polyhalide ion, I_2, Br_2 and F_2, wherein said slurry provides a selectivity for a CMP process of at least approximately 200 for removal of said copper or silver film relative to said barrier film~~.

38. (Cancelled)

39. (Cancelled)

40. (Cancelled)

41. (Cancelled)

42. (Cancelled)

43. (Cancelled)